



FZT1147A

12V PNP MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features and Benefits

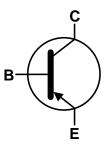
- BV_{CEO} > -12V
- Maximum Continuous Current I_C = -5A
- Peak Pulse Current I_C = -20A
- High Gain Holds Up h_{FE} > 200 @ I_C = -2A
- Very Low Equivalent On-Resistance; R_{CE(sat)} = 85mΩ at -2A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

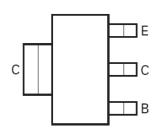
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)







Device Symbol



Top View Pin Out

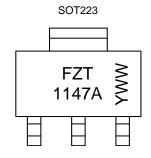
Ordering Information (Note 4)

Ī	Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	FZT1147ATA	AEC-Q101	FZT1147A	7	12	1.000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 1147A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 6 = 2016) WW or $\overline{W}W$ = Week Code (01 to 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-15	V
Collector-Emitter Voltage	V _{CEO}	-12	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-5	Α
Base Current	Ι _Β	-500	mA
Peak Pulse Current	I _{CM}	-20	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	D	2.0	W	
Power Dissipation	(Note 7)	P_{D}	1.6		
	(Note 8)	1	1.2		
	(Note 5)		41.7		
Thermal Begintance, Junction to Ambient	(Note 6)	Б	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note		$R_{ hetaJL}$	10.9		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

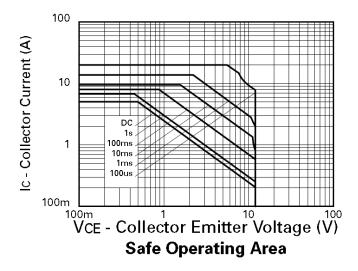
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

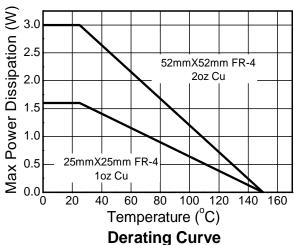
Notes:

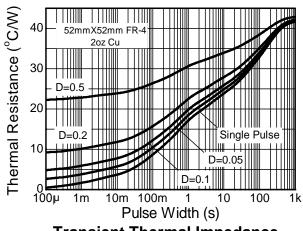
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as note (5), except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

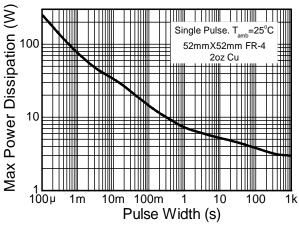


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

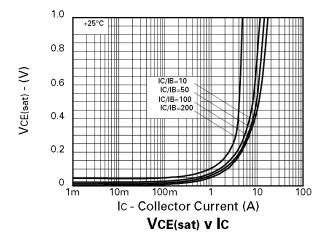
Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	-15	-35	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CES}	-12	-25	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-12	-25	-	V	$I_C = -10mA$
Collector-Emitter Breakdown Voltage	BV _{CEV}	-12	-25	-	V	$I_C = -100 \mu A$, $V_{EB} = -1 V$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.5	-	V	$I_E = -100 \mu A$
Collector Cut Off Current	I _{CBO}	-	-0.3	-100	nA	V _{CB} = -12V
Collector Cut Off Current	I _{CES}	-	-0.3	-100	nA	V _{CES} = -10V
Emitter Cut Off Current	I _{EBO}	-	-0.3	-100	nA	V _{EB} = -6V
		270	450	-	-	$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
	hFE	250	400	850		$I_C = -0.5A$, $V_{CE} = -2V$
DC Current Transfer Static Ratio (Note 11)		200	340	-		$I_C = -2A$, $V_{CE} = -2V$
De Current Hansier Static Natio (Note 11)		150	245	-		$I_C = -5A$, $V_{CE} = -2V$
		90	145	-		$I_C = -10A$, $V_{CE} = -2V$
		-	50	-		$I_C = -20A$, $V_{CE} = -2V$
	V _{CE(sat)}	-	-25	-50	mV	$I_C = -0.1A, I_B = -1mA$
		-	-70	-110		$I_C = -0.5A$, $I_B = -2.5mA$
Collector-Emitter Saturation Voltage (Note 11)		-	-90	-130		$I_C = -1A, I_B = -6mA$
		-	-115	-170		$I_C = -2A$, $I_B = -20mA$
		-	-250	-400		$I_C = -5A$, $I_B = -50mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	-	-950	-1,050	mV	$I_C = -5A$, $I_B = -50mA$
Base-Emitter Turn-on Voltage (Note 11)	$V_{BE(on)}$	-	-905	-1,000	mV	$I_C = -5A$, $V_{CE} = -2V$
Transitional Frequency	f⊤	-	115	-	MHz	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V},$ f = 50 MHz
Output Capacitance	C _{obo}	-	80	-	pF	V _{CB} = -10V, f = 1MHz
Switching Time	t _{ON}	-	150	-	ns	$V_{CC} = -10V, I_C = -4A,$
Switching Time	t _{OFF}	-	220	-	ns	$-I_{B1} = I_{B2} = 40 \text{mA}$

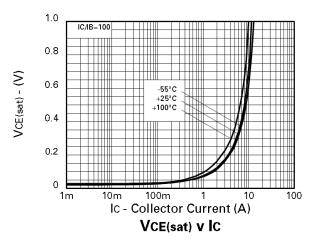
Note: 11. Measured under pulsed conditions. Pulse width = 300 μ s. Duty cycle \leq 2%.

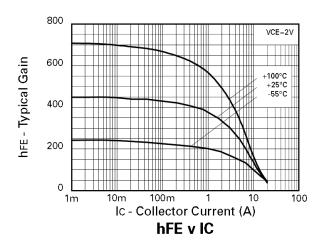
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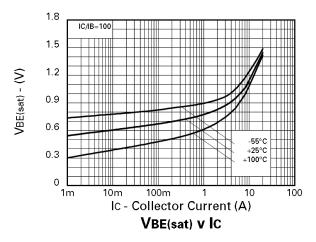


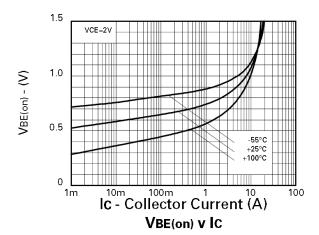
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)









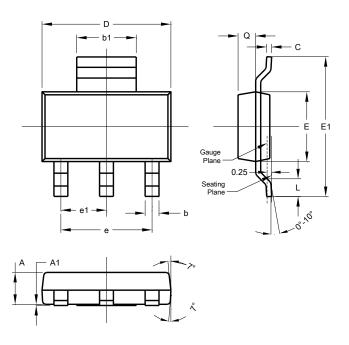




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

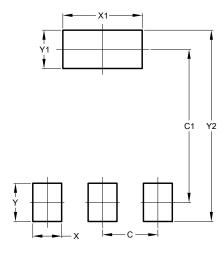


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8 00



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